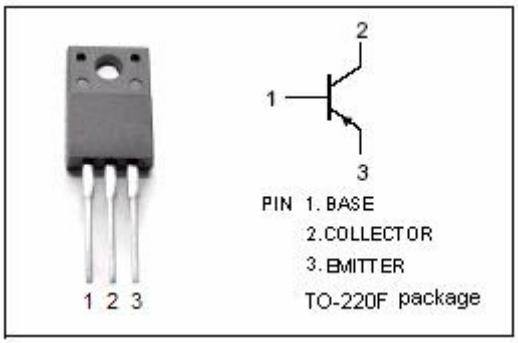
isc Silicon PNP Power Transistor 2SA1932

DESCRIPTION

- High collector breakdown voltage
- Complementary to 2SC5174
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

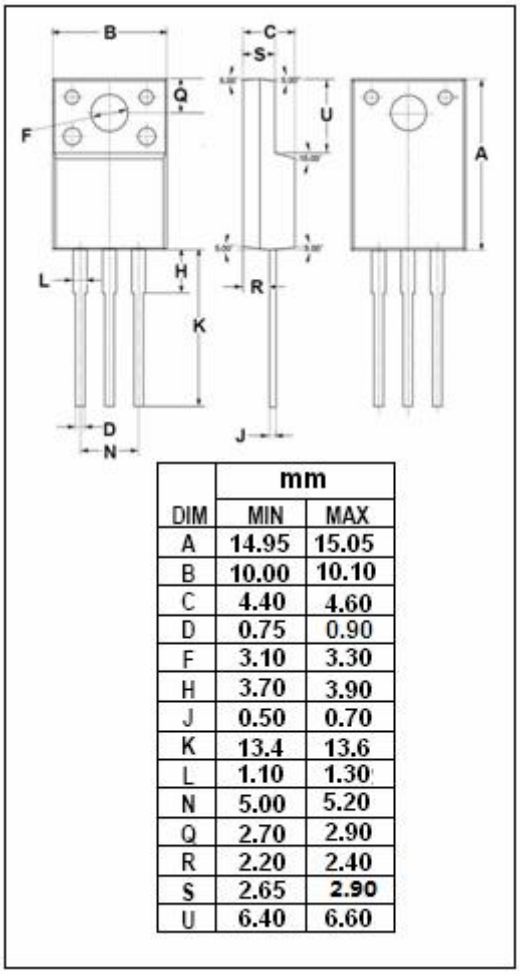


APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-230	V
V_{CEO}	Collector-Emitter Voltage	-230	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1	A
I_B	Base Current-Continuous	-0.1	A
P_C	Collector Power Dissipation @T_a=25℃	1.8	W
	Collector Power Dissipation @T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-230			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.5	V
$V_{BE(ON)}$	Base-Emitter on Voltage	I_C= -500mA;V_{CE}=-5V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -230V ; I_E=0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C=0			-1.0	μA
h_{FE}	DC Current Gain	I_C= -100mA; V_{CE}= -5V	100		320	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		30		pF
f_T	Current-Gain—Bandwidth Product	I_C= -100mA ; V_{CE}= -10V		70		MHz